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DISPLAY DEVICE AND METHOD OF
MANUFACTURING THE SAME****Publication Classification**

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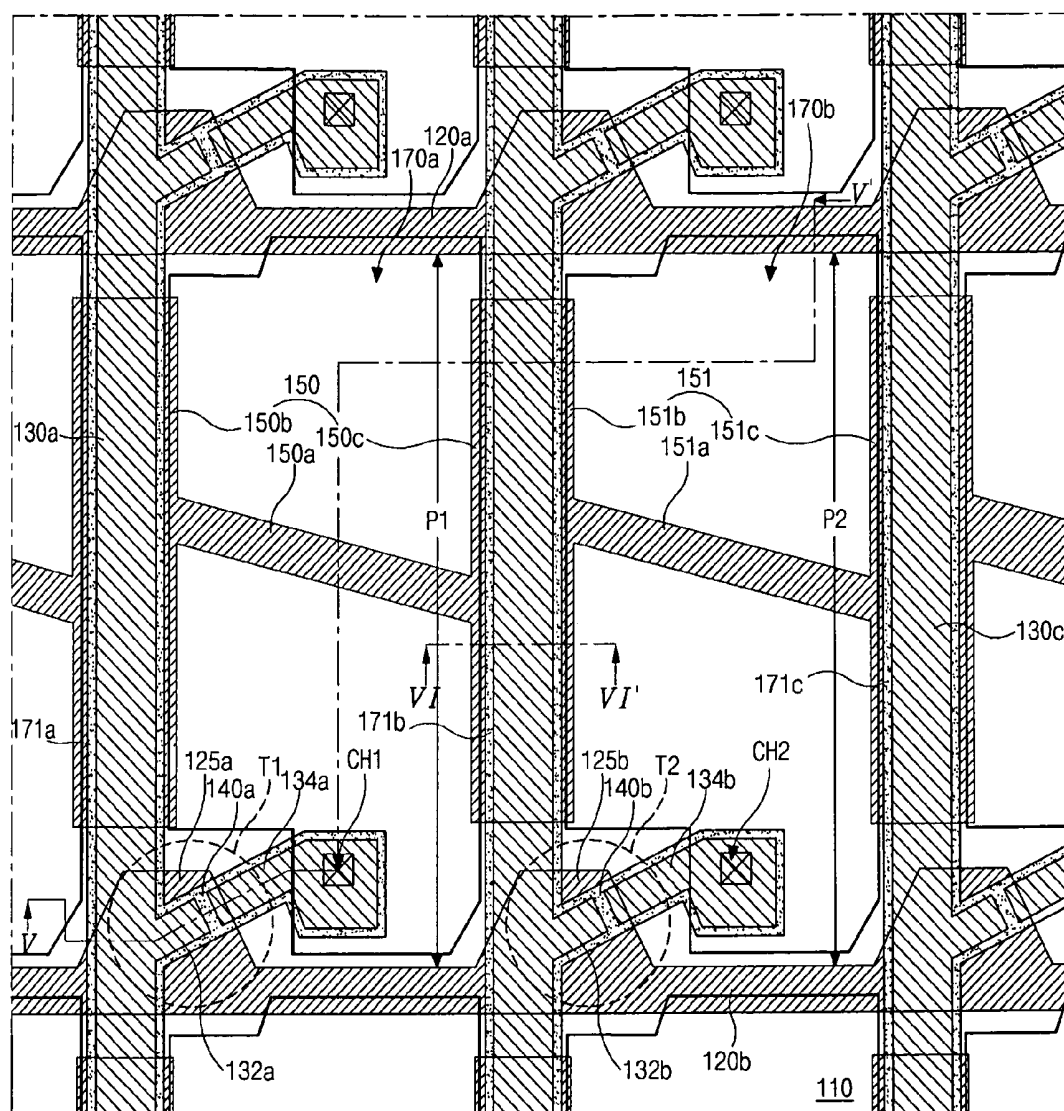
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ABSTRACT

A LCD device including a substrate, first and second gate lines along a first direction, first through third data lines along a second direction and crossing the first and second gate lines to define first and second pixel regions, first and second TFT's at a crossing of the second gate line and the first data line and a crossing of the second gate line and the second data line, first and second pixel electrodes in the first and second pixel regions, the first pixel electrode connected to the first TFT and the second pixel electrode connected to the second TFT, and first and second common lines between the first and second gate lines and overlapping the first and second pixel electrodes, and connected to each other under the second data line to cover a part of the second data line between the first and second gate lines.



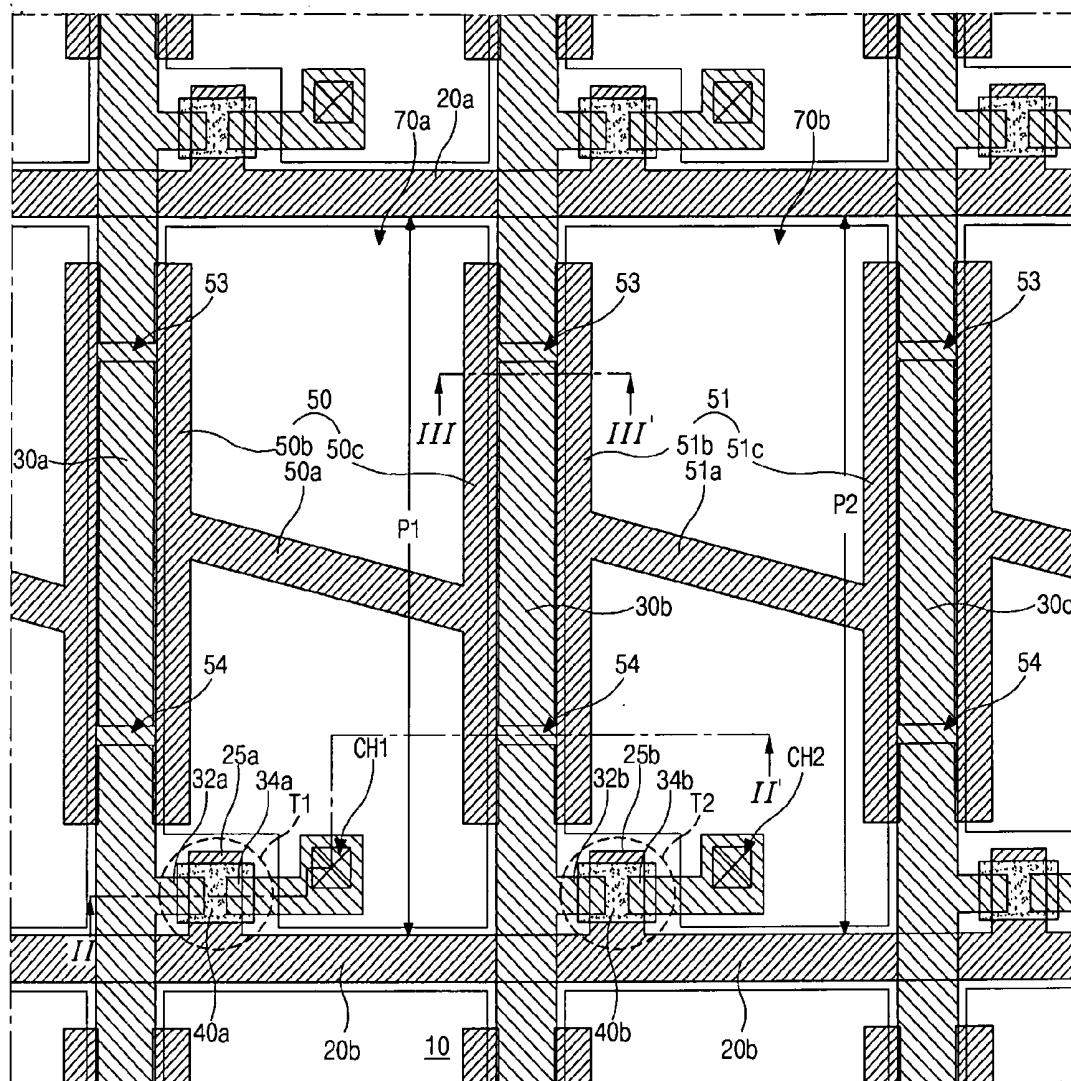


FIG. 1
RELATED ART

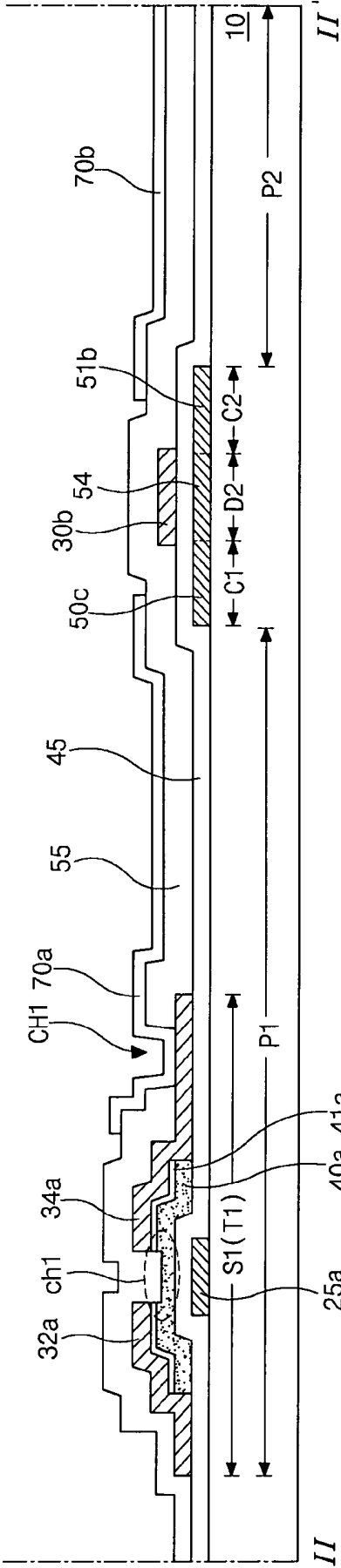


FIG. 2
RELATED ART

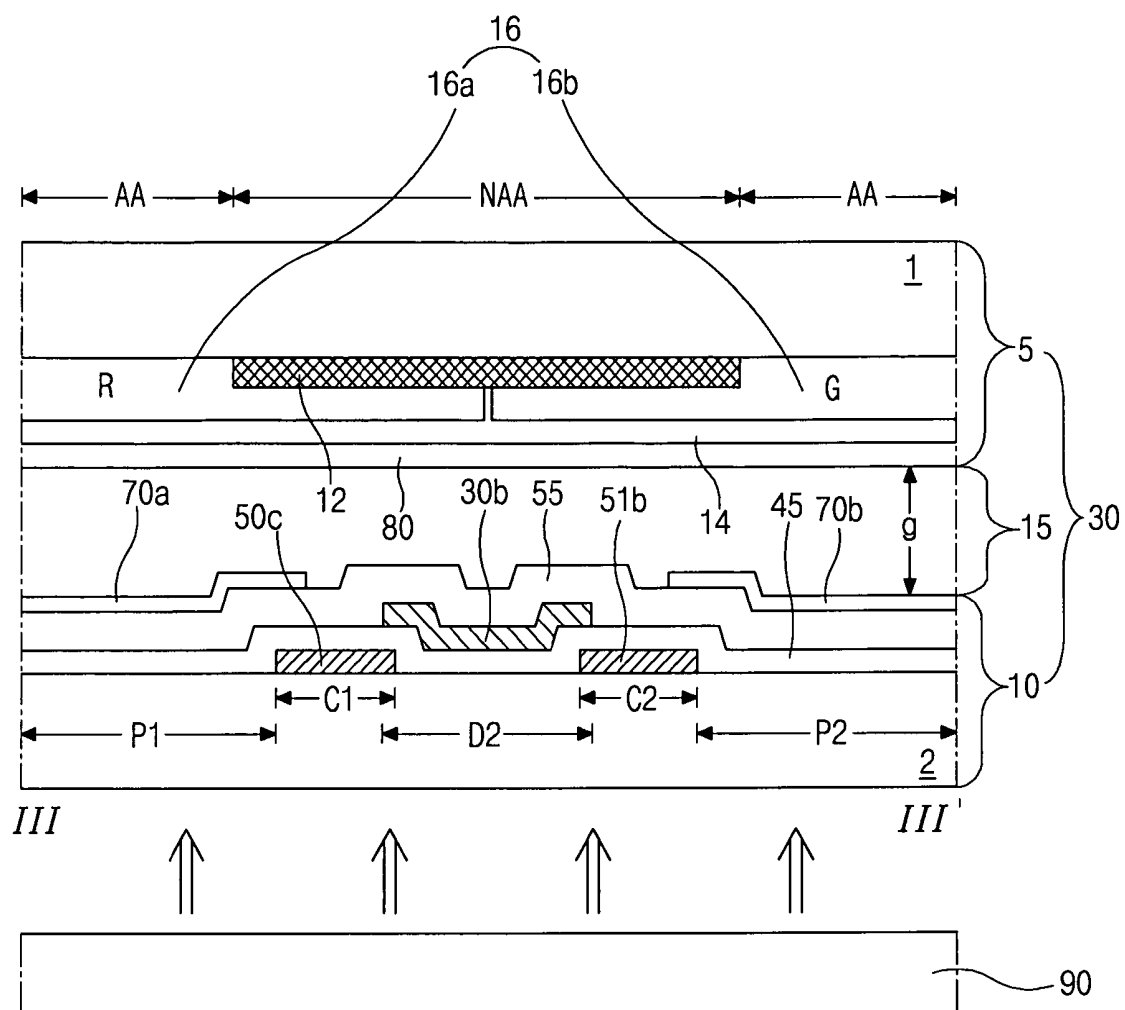


FIG. 3
RELATED ART

FIG. 4

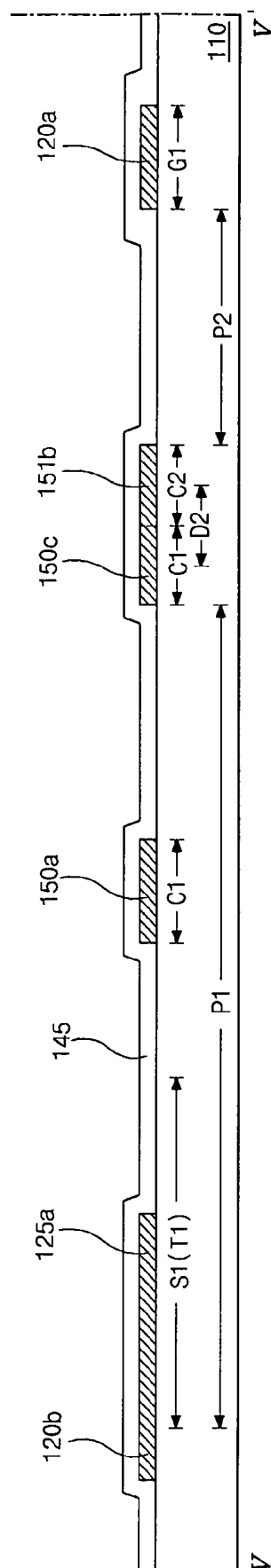


FIG. 5A

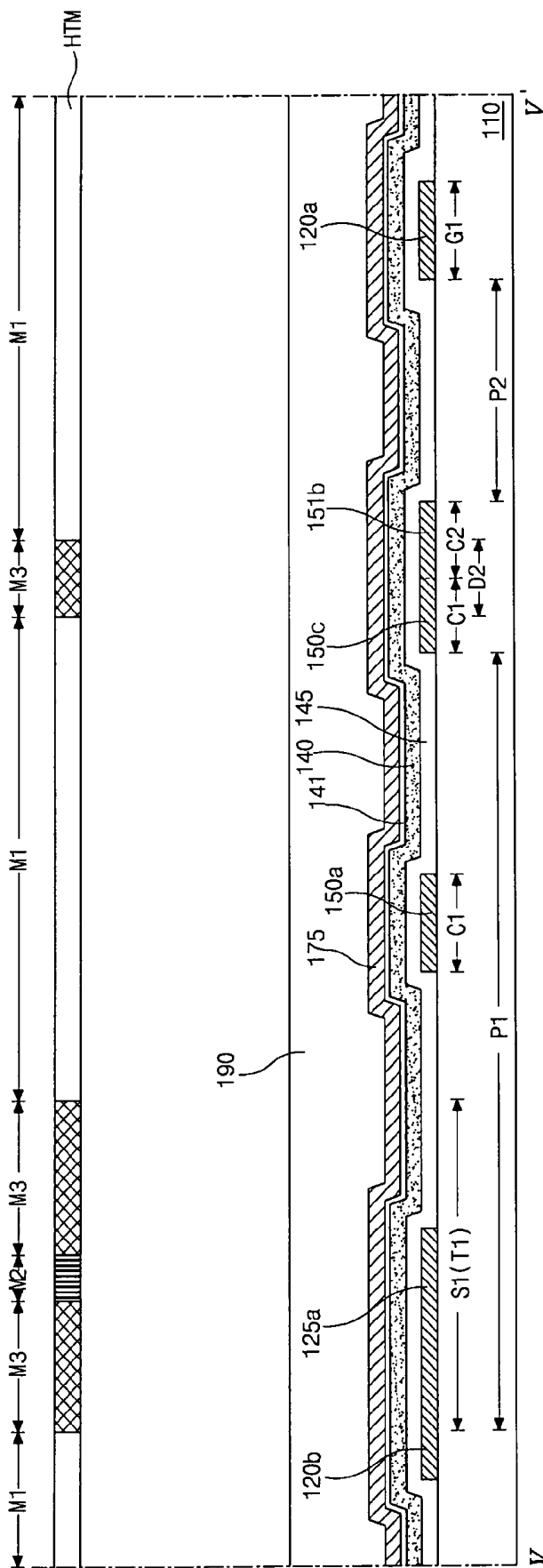


FIG. 5B

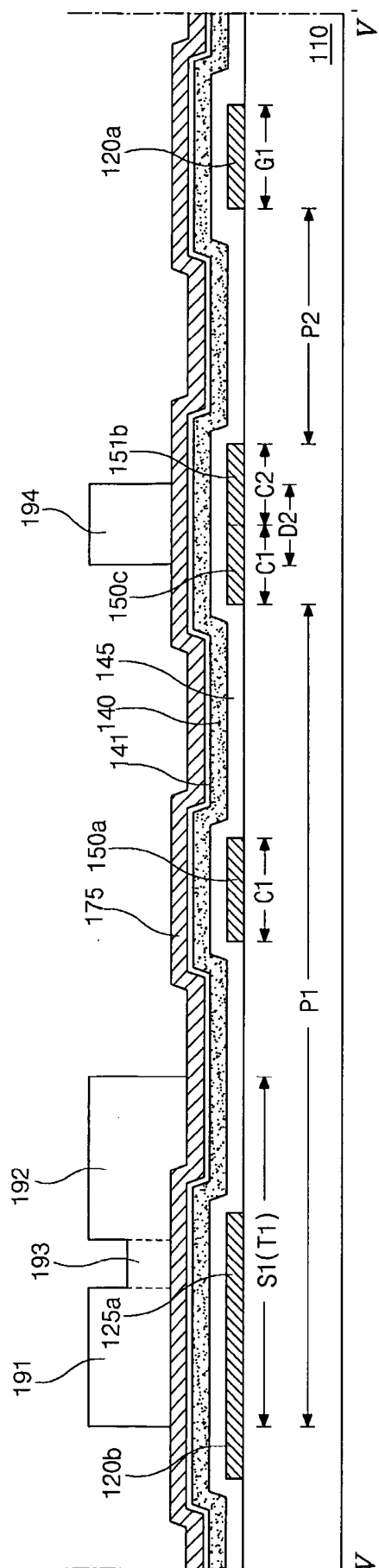


FIG. 5C

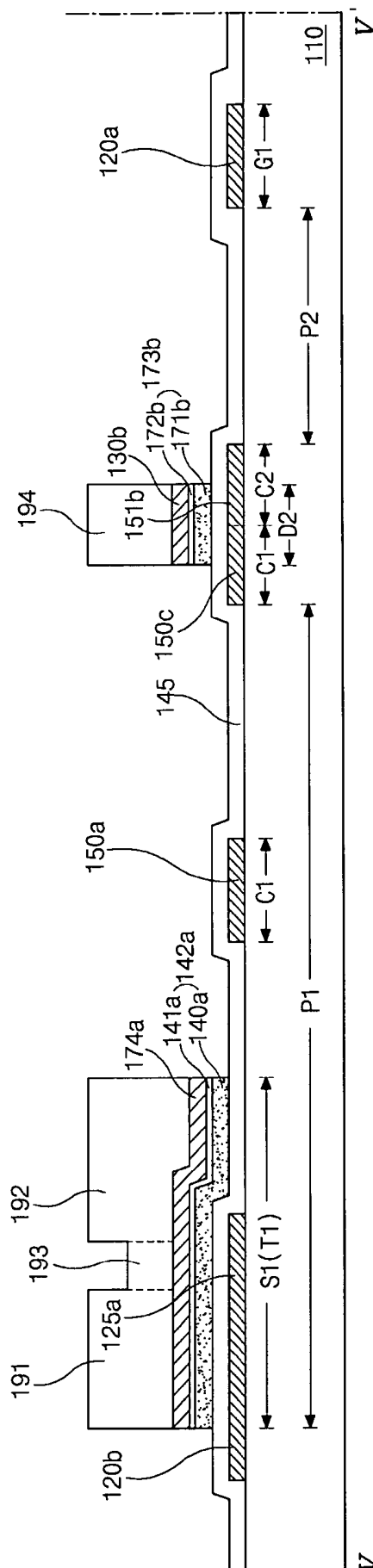


FIG. 5D

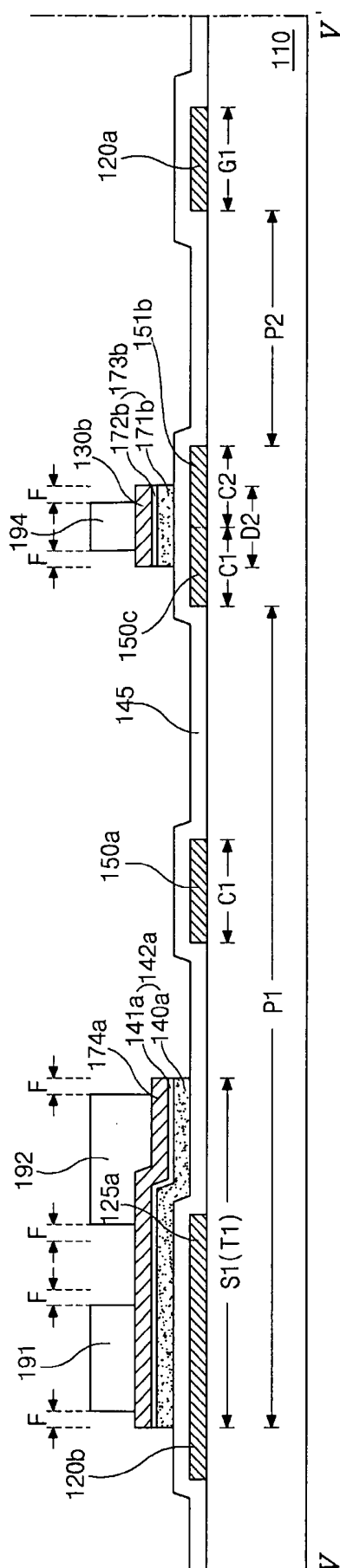


FIG. 5B

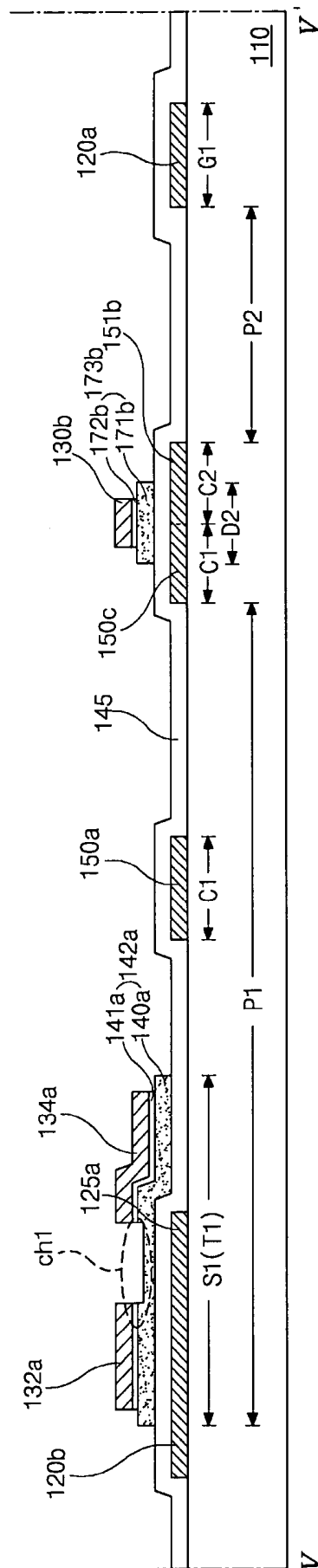


FIG. 5F

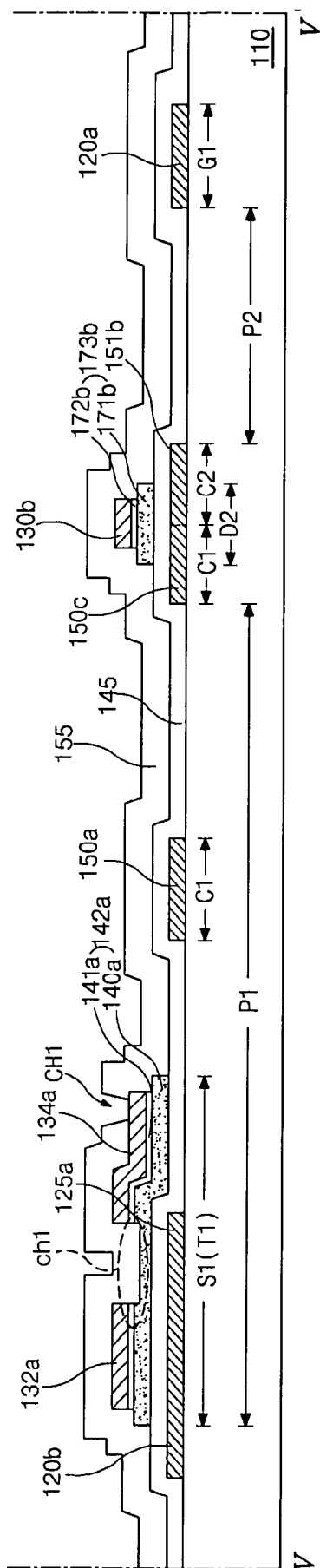


FIG. 5G

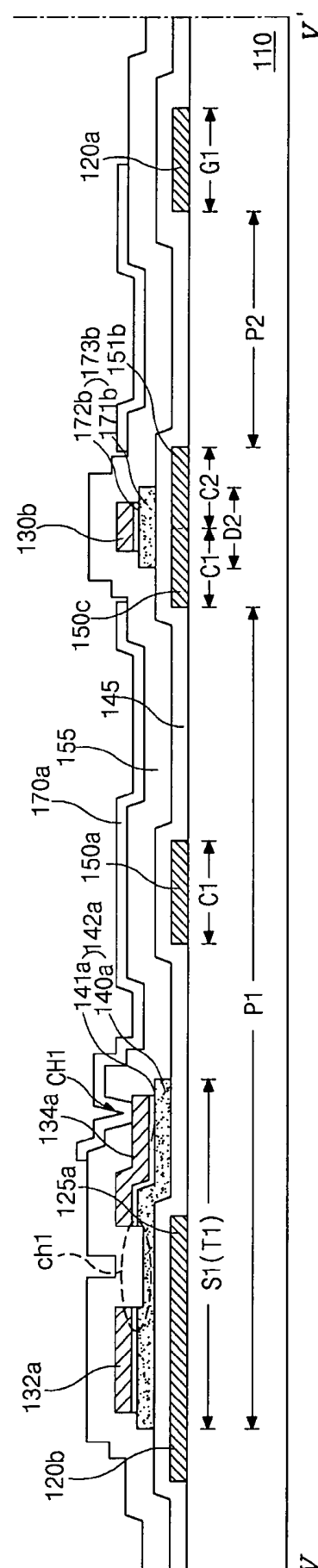


FIG. 5H

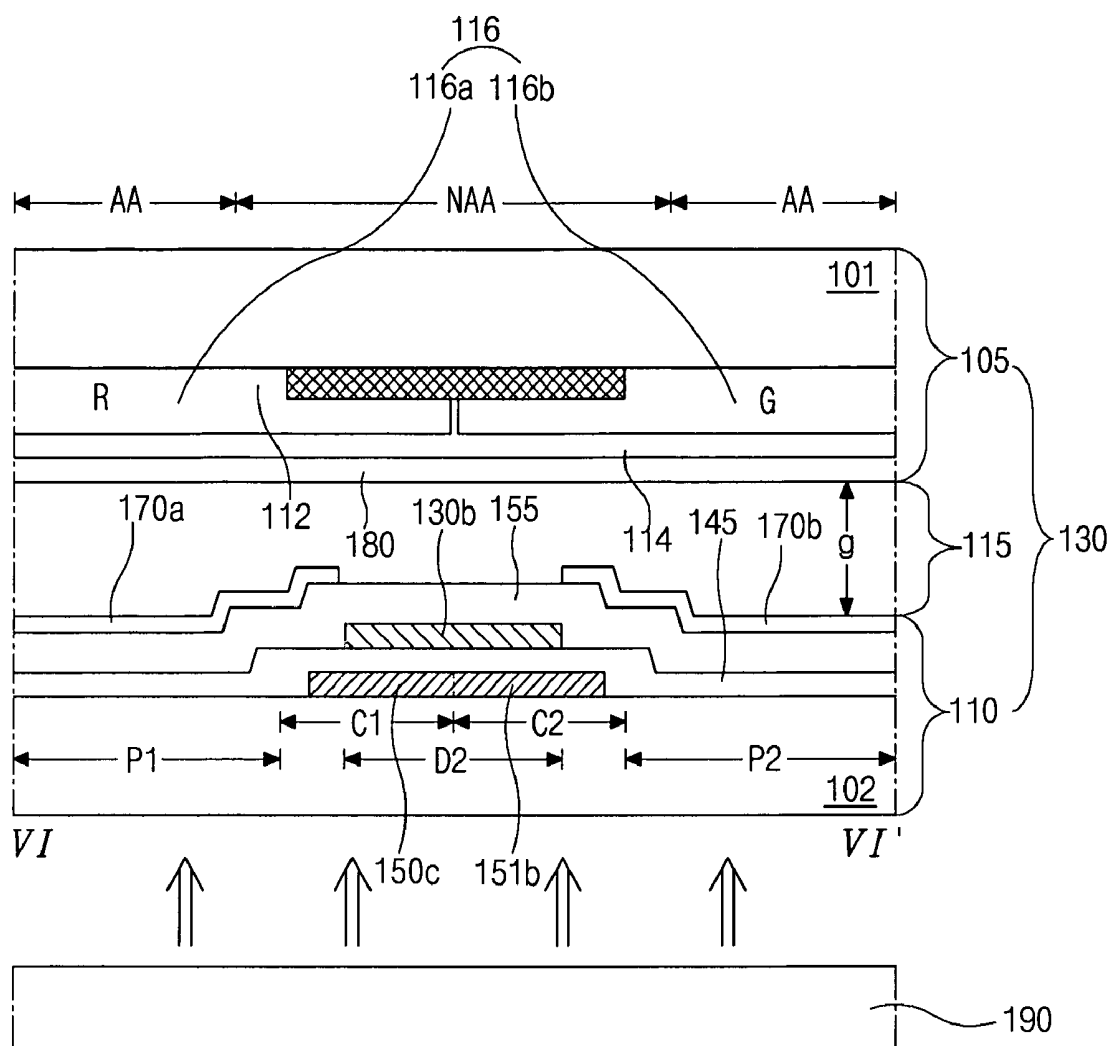


FIG. 6

ARRAY SUBSTRATE FOR LIQUID CRYSTAL DISPLAY DEVICE AND METHOD OF MANUFACTURING THE SAME

[0001] The invention claims the benefit of Korean Patent Application No. 10-2008-0055370 filed in Korea on Jun. 12, 2008, which is hereby incorporated by reference for all purposes as if fully set forth herein.

BACKGROUND OF THE INVENTION

[0002] 1. Field of the Invention

[0003] The invention relates to a liquid crystal display device, and more particularly, to an array substrate for a liquid crystal display device and a method of manufacturing the same.

[0004] 2. Discussion of the Related Art

[0005] Liquid crystal display (LCD) devices use the optical anisotropy and polarization properties of liquid crystal molecules of a liquid crystal layer to produce an image. The liquid crystal molecules have long, thin shapes, and the liquid crystal molecules can be arranged along a certain direction. The alignment direction of the liquid crystal molecules can be controlled by varying the intensity of an electric field applied to the liquid crystal layer. Accordingly, the alignment of the liquid crystal molecules is changed by the electric field. Light is transmitted and refracted according to the alignment of the liquid crystal molecules to display an image.

[0006] A liquid crystal display device includes a color filter substrate having a common electrode, an array substrate having a pixel electrode, and a liquid crystal layer interposed between two substrates. The liquid crystal display device is driven by a vertical electric field induced between the common electrode and the pixel electrode and has superior transmittance and aperture ratio.

[0007] The pixel electrode of the array substrate and the common electrode of the color filter substrate form a liquid crystal capacitor. A voltage applied to the liquid crystal capacitor is not maintained until a next signal is provided and is leaked. Accordingly, to maintain the applied voltage, a storage capacitor is connected to the liquid crystal capacitor.

[0008] Generally, the storage capacitor can be formed by two methods. One method may be referred to as a storage-on-common or independent storage capacitor type, in which an electrode for the storage capacitor is further formed and is connected to the common electrode. The other method may be referred to as a storage-on-gate or previous gate type, in which a part of an (n-1)th gate line is used as an electrode for the storage capacitor of an nth pixel.

[0009] The storage-on-gate type has an advantage that an outer storage line is not needed because a signal for the storage capacitor is applied through the gate line. However, the storage-on-gate type has a disadvantage in that there is signal interference due to coupling with a gate signal.

[0010] On the other hand, the storage-on-common (SOC) type has an advantage in that there is no signal interference in the gate signal and an enough storage capacitance can be secured. However, a storage line is further formed, and this causes a decrease in the aperture ratio.

[0011] A related art SOC type liquid crystal display (LCD) device will be explained with reference to the accompanying drawings.

[0012] FIG. 1 is a plan view illustrating an array substrate for an SOC-type LCD device according to the related art.

[0013] In FIG. 1, first and second gate lines **20a** and **20b** and first, second, and third data lines **30a**, **30b** and **30c** are formed on a substrate **10** in a matrix shape. The first, second and third data lines **30a**, **30b** and **30c** cross the first and second gate lines **20a** and **20b** to define first and second pixel regions **P1** and **P2**. Scan signals are applied to the first and second gate lines **20a** and **20b**, and data signals are applied to the first, second and third data lines **30a**, **30b** and **30c**.

[0014] First and second common lines **50** and **51** are formed between the first and second gate lines **20a** and **20b**. Each of the first and second common lines **50** and **51** has an H-like shape.

[0015] The first common line **50** includes a horizontal part **50a** and first and second vertical parts **50b** and **50c**. The horizontal part **50a** is disposed in the first pixel region **P1** along a horizontal direction in the context of the figure. The first and second vertical parts **50b** and **50c** extend from respective ends of the horizontal part **50a** along a vertical direction in the context of the figure. The first and second vertical parts **50b** and **50c** are parallel with the data lines **30a**, **30b** and **30c** and are adjacent to the first and second data lines **30a** and **30b**, respectively.

[0016] The second common line **51** also includes a horizontal part **51a** and first and second vertical parts **51b** and **51c**. The horizontal part **51a** is disposed in the second pixel region **P2** along the horizontal direction in the context of the figure. The first and second vertical parts **51b** and **51c** extend from respective ends of the horizontal part **51a** along the vertical direction in the context of the figure. The first and second vertical parts **51b** and **51c** are parallel with the data lines **30a**, **30b** and **30c** and are adjacent to the second and third data lines **30b** and **30c**, respectively.

[0017] The second vertical part **50c** of the first common line **50** is connected to the first vertical part **51b** of the second common line **51** through first and second common bridge lines **53** and **54**. The first and second common bridge lines **53** and **54** are repeatedly formed between adjacent pixel regions and connect the common lines in adjacent pixel regions. Accordingly, all the common lines on the substrate **10** are electrically connected to one another through the first and second common bridge lines **53** and **54**, and a common signal from a common signal generating unit (not shown) is applied to all the common lines on the substrate **10**.

[0018] A first thin film transistor **T1** is formed at a crossing portion of the second gate line **20b** and the first data line **30a**. A second thin film transistor **T2** is formed at a crossing portion of the second gate line **20b** and the second data line **30b**.

[0019] The first thin film transistor **T1** includes a first gate electrode **25a**, a first semiconductor layer (not shown), a first source electrode **32a** and a first drain electrode **34a**. The first gate electrode **25a** extends from the second gate line **20b** into the first pixel region **P1**. The first semiconductor layer (not shown) overlaps and is disposed over the first gate electrode **25a**. The first source electrode **32a** extends from the first data line **30a** and is disposed over the first semiconductor layer. The first drain electrode **34a** is spaced apart from the first source electrode **32a**.

[0020] The second thin film transistor **T2** includes a second gate electrode **25b**, a second semiconductor layer (not shown), a second source electrode **32b** and a second drain electrode **34b**. The second gate electrode **25b** extends from the second gate line **20b** into the second pixel region **P2**. The second semiconductor layer (not shown) overlaps and is dis-

posed over the second gate electrode **25b**. The second source electrode **32b** extends from the second data line **30b** and is disposed over the second semiconductor layer. The second drain electrode **34b** is spaced apart from the second source electrode **32b**.

[0021] The first semiconductor layer includes a first active layer **40a** of intrinsic amorphous silicon (a-Si:H) and a first ohmic contact layer (not shown) of impurity-doped amorphous silicon (n+ a-Si:H). The second semiconductor layer includes a second active layer **40b** of intrinsic amorphous silicon (a-Si:H) and a second ohmic contact layer (not shown) of impurity-doped amorphous silicon (n+ a-Si:H).

[0022] First and second contact holes CH1 and CH2 expose the first and second drain electrodes **34a** and **34b**, respectively.

[0023] First and second pixel electrodes **70a** and **70b** are formed in the first and second pixel regions P1 and P2, respectively. The first pixel electrode **70a** contacts the first drain electrode **34a** through the first drain contact hole CH1. The second pixel electrode **70b** contacts the second drain contact hole **34b** through the second drain contact hole CH2. The first and second pixel electrodes **70a** and **70b** are formed of one selected from a transparent conductive material group including indium tin oxide (ITO) and indium zinc oxide (IZO).

[0024] A cross-sectional structure of an array substrate for an SOC-type LCD device according to the related art will be explained with reference to the accompanying drawings.

[0025] FIG. 2 is a cross-sectional view taken along the line II-II' of FIG. 1.

[0026] In FIG. 2, the first and second pixel regions P1 and P2, a first switching region S1, first and second common regions C1 and C2, and a second data region D2 are defined on the substrate **10**.

[0027] The first gate electrode **25a** extending from the second gate line **20b** of FIG. 1 is formed on the substrate **20** including the regions P1, P2, S1, C1, C2 and D2. In addition, the second vertical part **50c** of the first common line **50** and the first vertical part **51b** of the second common line **51** are formed in the first and second common regions C1 and C2, respectively. The second common bridge line **54** is formed between the second vertical part **50c** of the first common line **50** and the first vertical part **51b** of the second common line **51**. The second common bridge line **54** electrically connects the second vertical part **50c** of the first common line **50** to the first vertical part **51b** of the second common line **51**.

[0028] A gate insulating layer **45** is formed on the first gate electrode **25a**, the second vertical part **50c** of the first common line **50**, the first vertical part **51b** of the second common line **51** and the second common bridge line **54**. The gate insulating layer **45** is formed of one selected from an inorganic insulating material group including silicon oxide (SiO₂) and silicon nitride (SiN_x).

[0029] The first active layer **40a** of intrinsic amorphous silicon and the first ohmic contact layer **41a** of impurity-doped amorphous silicon are sequentially formed on the gate insulating layer **45** overlapping the first gate electrode **25a**. The first active layer **40a** and the first ohmic contact layer **41a** have an island shape and constitute the first semiconductor layer **42a**.

[0030] The first source electrode **32a** and the first drain electrode **34a** are formed on the first semiconductor layer **42a**. The first source electrode **32a** extends from the first data line **30a** of FIG. 1. The first drain electrode **34a** is spaced apart from the first source electrode **32a**. In addition, the second

data line **30b** is formed in the second data region D2 and overlaps the second common bridge line **54**.

[0031] A passivation layer **55** is formed on the first source electrode **32a**, the first drain electrode **34a** and the second data line **30b**. The passivation layer **55** has the first drain contact hole CH1 exposing the first drain electrode **34a**.

[0032] The first pixel electrode **70a** and the second pixel electrode **70b** are formed on the passivation layer **55**. The first pixel electrode **70a** is disposed in the first pixel region P1 and is connected to the first drain electrode **34a** through the first drain contact hole CH1. The second pixel electrode **70b** is disposed in the second pixel region P2 and is connected to the second drain electrode **34b** of FIG. 1 through the second drain contact hole CH2 of FIG. 1.

[0033] Here, the second vertical part **50c** of the first common line **50** and the first vertical part **51b** of the second common line **51** are disposed to be as close to the second data line **30b** as possible, and the second common bridge line **54** connects the second vertical part **50c** of the first common line **50** and the first vertical part **51b** of the second common line **51**. The first pixel electrode **70a** partially overlaps the first vertical part **50b** of FIG. 1 and the second vertical part **50c** of the first common line **50**, and the second pixel electrode **70b** partially overlaps the first vertical part **51b** and the second vertical part **51c** of FIG. 1 of the second common line **51**.

[0034] However, in the above-mentioned array substrate, there is a limitation on increasing the aperture ratio.

[0035] FIG. 3 is a cross-sectional view of an SOC-type LCD device according to the related art and corresponds to a cross-section taken along the line III-III' of FIG. 1.

[0036] In FIG. 3, a color filter substrate **5** and an array substrate **10** are facing each other and attached with a cell gap g therebetween. Each of the color filter substrate **5** and the array substrate **10** includes a display area AA and a non-display area NAA. A liquid crystal layer **15** is interposed between the color filter substrate **5** and the array substrate **10**. The liquid crystal layer **15** has a thickness corresponding to the cell gap g. The color filter substrate **5**, the array substrate **10** and the liquid crystal layer **15** constitute a liquid crystal panel **30**. A backlight unit **90** is disposed at a rear surface of the array substrate **10** as a light source.

[0037] Even though not shown in the figure, a seal pattern is formed between the color filter substrate **5** and the array substrate **10** along peripheries. The seal pattern may be formed of a thermosetting resin.

[0038] The color filter substrate **5** includes a transparent substrate **1**, a black matrix **12**, a color filter layer **16**, an overcoat layer **14** and a common electrode **80**. The black matrix **12** is formed at a lower surface of the transparent substrate **1** and blocks light incident on the non-display area NAA. The color filter layer **16** is formed on the black matrix **12** and includes a red sub color filter **16a**, a green sub color filter **16b** and a blue sub color filter (not shown) that are subsequently patterned. The overcoat layer **14** is formed on the color filter layer **16**. The common electrode **80** is formed on the overcoat layer **14** and is formed of a transparent conductive material.

[0039] The array substrate **10** includes a transparent substrate **2**, the second vertical part **50c** of the first common line, the first vertical part **51b** of the second common line **51**, the gate insulating layer **45**, the second data line **30b**, the passivation layer **55**, and the first and second pixel electrodes **70a** and **70b**. The second vertical part **50c** of the first common line **50** and the first vertical part **51b** of the second common line **51**

are formed on an upper surface of the transparent substrate 2 and are spaced apart from each other such that the second data region D2 is disposed therebetween. The gate insulating layer 45 covers the second vertical part 50c of the first common line 50 and the first vertical part 51b of the second common line 51. The second data line 30b is disposed in the second data line D2 on the gate insulating layer 45. The passivation layer 55 covers the second data line 30b. The first and second pixel electrodes 70a and 70b are formed on the passivation layer 55 in the first and second pixel regions P1 and P2, respectively, such that the second data line 30b is disposed therebetween.

[0040] In the SOC-type LCD device, since the second vertical part 50c of the first common line 50 and the first vertical part 51b of the second common line 51 are formed under the second data line 30b, there is no poor image problem such as crosstalk, which is caused by a change of a data signal due to a parasitic capacitance between the first and second pixel electrodes 70a and 70b and the second data line 30b, even if the first and second pixel electrodes 70a and 70b are close to the second data line 30b. However, the aperture ratio is lowered because the second vertical part 50c of the first common line 50 and the first vertical part 51b of the second common line 51 are spaced apart from each other.

[0041] Moreover, the black matrix 12, which is disposed in the non-display area NAA on the lower surface of the transparent substrate 1 of the color filter substrate 5, is designed with an attachment margin of about 2 μ m at both ends to cover the second vertical part 50c of the first common line 50 and the first vertical part 51b of the second common line 51 by considering an attachment error when the color filter substrate 5 and the array substrate 10 are attached. Accordingly, the aperture ratio is further reduced by the attachment margin.

[0042] Furthermore, in the SOC-type LCD device having a small size, for example, less than 10 inches, attempts for reducing costs have been made by increasing the aperture ratio of the liquid crystal panel 30 and removing optical sheets of the backlight 90.

[0043] However, the second vertical part 50c of the first common line 50 and the first vertical part 51b of the second common line 51 are spaced apart from each other at both sides of the second data line 30b and are connected to each other through the first and second common bridge lines 53 and 54 of FIG. 1 overlapping the second data line 30b. It is restricted to decrease a distance between the second vertical part 50c of the first common line 50 and the first vertical part 51b of the second common line 51 because of a limitation in a resolution of a light-exposing apparatus. Therefore, it is difficult to increase the aperture ratio.

[0044] Accordingly, the prevention invention is directed to an array substrate for a liquid crystal display device and method of manufacturing the same that substantially obviates one or more of the problems due to limitations and disadvantages of the related art.

SUMMARY OF THE INVENTION

[0045] An advantage of the invention is to provide an array substrate for a liquid crystal display device includes a substrate, first and second gate lines along a first direction on the substrate, first, second and third data lines along a second direction and crossing the first and second gate lines to define first and second pixel regions, first and second thin film transistors at a crossing portion of the second gate line and the first data line and at a crossing portion of the second gate line and the second data line, respectively, first and second pixel elec-

trodes in the first and second pixel regions, respectively, the first pixel electrode connected to the first thin film transistor and the second pixel electrode connected to the second thin film transistor, and first and second common lines between the first and second gate lines, the first and second common lines overlapping the first and second pixel electrodes, respectively, and connected to each other under the second data line to cover a part of the second data line between the first and second gate lines.

[0046] In another aspect, a method of manufacturing an array substrate for a liquid crystal display device includes steps of defining first and second switching regions, first and second pixel regions, first and second common regions, and first, second and third data regions on a substrate, forming first and second gate lines, first and second gate electrodes, and first and second common lines on the substrate, wherein the first and second gate lines are formed along a first direction, the first and second gate electrodes are connected to the second gate line, and the first and second common lines are disposed in the first and second common regions, respectively, forming a gate insulating layer on the first and second gate lines, the first and second gate electrodes, and the first and second common lines, forming first and second semiconductor layers on the gate insulating layer over the first and second gate electrodes, forming first, second and third data lines, first and second source electrodes, and first and second drain electrodes over the first and second semiconductor layers, wherein the first, second and third data lines are formed along a second direction and cross the first and second gate lines to define the first and second pixel regions, the first source and drain electrodes are spaced apart from each other over the first semiconductor layer, and the second source and drain electrodes are spaced apart from each other over the second semiconductor layer, forming a passivation layer on the first, second and third data lines, the first and second source electrodes, and the first and second drain electrodes, the passivation layer including first and second contact holes that expose the first and second drain electrodes, respectively, and forming first and second pixel electrodes on the passivation layer, the first pixel electrode connected to the first drain electrode through the first contact hole, and the second pixel electrode connected to the second drain electrode through the second contact hole, wherein the first and second common lines overlap the first and second pixel electrodes, respectively and are connected to each other under the second data line to cover a part of the second data line between the first and second gate lines.

[0047] In another aspect, an array substrate for a liquid crystal display device includes a substrate, a gate line along a first direction on the substrate, a data line along a second direction and crossing the gate line to define a pixel region, a thin film transistor at a crossing portion of the gate line and the data line, a pixel electrode in the pixel region and connected to the thin film transistor, and a common line between adjacent gate lines and overlapping the pixel electrode, the common line including a horizontal portion along the first direction and first and second vertical portions along the second direction, wherein the first vertical portion of the common line directly contacts a second vertical portion of a common line in a next pixel region under the data line to thereby cover a part of the data line between the adjacent gate lines.

[0048] It is to be understood that both the foregoing general description and the following detailed description are exem-

plary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0049] The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification, illustrate embodiments of the invention and together with the description serve to explain the principles of the invention.

[0050] In the drawings:

[0051] FIG. 1 is a plan view illustrating an array substrate for an SOC-type LCD device according to the related art;

[0052] FIG. 2 is a cross-sectional view taken along the line II-II' of FIG. 1;

[0053] FIG. 3 is a cross-sectional view of an SOC-type LCD device according to the related art and corresponds to a cross-section taken along the line III-III' of FIG. 1;

[0054] FIG. 4 is a plan view illustrating an array substrate for an SOC-type LCD device according to an exemplary embodiment of the present invention;

[0055] FIGS. 5A to 5H are cross-sectional views of an array substrate corresponding to the line V-V' of FIG. 4; and

[0056] FIG. 6 is a cross-sectional view of an SOC-type LCD device according to the present invention and corresponds to a cross-section taken along the line VI-VI' of FIG. 4.

DETAILED DESCRIPTION OF THE ILLUSTRATED EMBODIMENTS

[0057] Reference will now be made in detail to embodiments of the present invention, examples of which are illustrated in the accompanying drawings.

[0058] In the present invention, a part of a data line between adjacent gate lines entirely overlaps a common line.

[0059] FIG. 4 is a plan view illustrating an array substrate for an SOC-type LCD device according to an exemplary embodiment of the present invention.

[0060] In FIG. 4, first and second gate lines **120a** and **120b** and first, second, third data lines **130a**, **130b** and **130c** are formed on a substrate **110** in a matrix shape. The first, second and third data lines **130a**, **130b** and **130c** cross the first and second gate lines **120a** and **120b** to define first and second pixel regions **P1** and **P2**. Scan signals are applied to the first and second gate lines **120a** and **120b**, and data signals are applied to the first, second and third data lines **130a**, **130b** and **130c**.

[0061] First and second common lines **150** and **151** are formed between the first and second gate lines **120a** and **120b**. Each of the first and second common lines **150** and **151** has an H-like shape.

[0062] The first common line **150** includes a horizontal part **150a** and first and second vertical parts **150b** and **150c**. The horizontal part **150a** is disposed between the first and second gate lines **120a** and **120b** and between the first and second data lines **130a** and **130b**. That is, the horizontal part **150a** is disposed in the first pixel region **P1** along a horizontal direction in the context of the figure. The first and second vertical parts **150b** and **150c** extend from respective ends of the horizontal part **150a** along a vertical direction in the context of the figure. The first and second vertical parts **150b** and **150c** are parallel with the data lines **130a**, **130b** and **130c** and are adjacent to the first and second data lines **130a** and **130b**, respectively.

[0063] The second common line **151** also includes a horizontal part **151a** and first and second vertical parts **151b** and **151c**. The horizontal part **151a** is disposed between the first and second gate lines **120a** and **120b** and between the second and third data lines **130b** and **130c**. That is, the horizontal part **151a** is disposed in the second pixel region **P2** along the horizontal direction in the context of the figure. The first and second vertical parts **151b** and **151c** extend from respective ends of the horizontal part **151a** along the vertical direction in the context of the figure. The first and second vertical parts **151b** and **151c** are parallel with the data lines **130a**, **130b** and **130c** and are adjacent to the second and third data lines **130b** and **130c**, respectively.

[0064] The horizontal part **150a** of the first common line **150** and the horizontal part **151a** of the first common line **151** may be slant with respect to the first and second gate lines **120a** and **120b**.

[0065] Here, the second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** overlap the second data line **130b** between the first gate line **120a** and the second gate line **120b**. The second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** cover the second data line **130b** excluding parts that cross the first gate line **120a** and the second gate line **120b**.

[0066] Even though the first and second pixel regions **P1** and **P2** are described, the first and second common lines **150** and **151** cover the first, second and data lines **130a**, **130b** and **130c** excluding parts that correspond to the thin film transistors of the pixel regions without the common bridge lines, which connect the common lines of adjacent pixel regions. A common signal from a common signal generating unit (not shown) is stably applied to the common lines of the pixel regions.

[0067] A first thin film transistor **T1** is formed at a crossing portion of the second gate line **120b** and the first data line **130a**. A second thin film transistor **T2** is formed at a crossing portion of the second gate line **120b** and the second data line **130b**.

[0068] The first thin film transistor **T1** includes a first gate electrode **125a**, a first semiconductor layer (not shown), a first source electrode **132a** and a first drain electrode **134a**. The first gate electrode **125a** extends from the second gate line **120b** into the first pixel region **P1**. The first semiconductor layer (not shown) overlaps and is disposed over the first gate electrode **125a**. The first source electrode **132a** extends from the first data line **130a** and is disposed over the first semiconductor layer. The first drain electrode **134a** is spaced apart from the first source electrode **132a**.

[0069] The second thin film transistor **T2** includes a second gate electrode **125b**, a second semiconductor layer (not shown), a second source electrode **132b** and a second drain electrode **134b**. The second gate electrode **125b** extends from the second gate line **120b** into the second pixel region **P2**. The second semiconductor layer (not shown) overlaps and is disposed over the second gate electrode **125b**. The second source electrode **132b** extends from the second data line **130b** and is disposed over the second semiconductor layer. The second drain electrode **134b** is spaced apart from the second source electrode **132b**.

[0070] The first semiconductor layer includes a first active layer **140a** of intrinsic amorphous silicon (a-Si:H) and a first ohmic contact layer (not shown) of impurity-doped amorphous silicon (n+ a-Si:H). The second semiconductor layer

includes a second active layer **140b** of intrinsic amorphous silicon (a-Si:H) and a second ohmic contact layer (not shown) of impurity-doped amorphous silicon (n+ a-Si:H).

[0071] First, second and third intrinsic amorphous silicon patterns **171a**, **171b** and **171c** and first, second and third impurity-doped amorphous silicon patterns (not shown) are also formed under the first, second and third data lines **130a**, **130b** and **130c**. The first, second and third intrinsic amorphous silicon patterns **171a**, **171b** and **171c** are formed on the same layer and of the same material as the first and second active layers **140a** and **140b**. The first, second and third impurity-doped amorphous silicon patterns are formed on the same layer and of the same material as the first and second ohmic contact layers.

[0072] The first, second and third intrinsic amorphous silicon patterns **171a**, **171b** and **171c** have wider widths than the first, second and third data lines **130a**, **130b** and **130c**, and thus parts of the first, second and third intrinsic amorphous silicon patterns **171a**, **171b** and **171c** are exposed beyond edges of the first, second and third data lines **130a**, **130b** and **130c**.

[0073] First and second contact holes **CH1** and **CH2** expose the first and second drain electrodes **134a** and **134b**, respectively.

[0074] First and second pixel electrodes **170a** and **170b** are formed in the first and second pixel regions **P1** and **P2**, respectively. The first pixel electrode **170a** contacts the first drain electrode **134a** through the first drain contact hole **CH1**. The second pixel electrode **170b** contacts the second drain contact hole **134b** through the second drain contact hole **CH2**. The first and second pixel electrodes **170a** and **170b** are formed of one selected from a transparent conductive material group including indium tin oxide (ITO) and indium zinc oxide (IZO). The first and second pixel electrodes **170a** and **170b** partially overlap the first gate line **120a**.

[0075] A first storage capacitor **Cst1** is formed, wherein the horizontal part **150a** and the first and second vertical parts **150b** and **150c** of the first common line **150** function as a first electrode of the first storage capacitor **Cst1**, the first pixel electrode **170a** overlapping the first electrode functions as a second electrode of the first storage capacitor **Cst1**, and an insulating layer (not shown) interposed between the first and second electrodes functions as a dielectric layer.

[0076] In addition, a second storage capacitor **Cst2** is formed, wherein the horizontal part **151a** and the first and second vertical parts **151b** and **151c** of the second common line **151** function as a first electrode of the second storage capacitor **Cst2**, the second pixel electrode **170b** overlapping the first electrode functions as a second electrode of the second storage capacitor **Cst2**, and an insulating layer (not shown) interposed between the first and second electrodes of the second storage capacitor **Cst2** functions as a dielectric layer.

[0077] A method of manufacturing an array substrate for an SOC-type LCD device according to the present invention will be explained with reference to accompanying drawings.

[0078] FIGS. 5A to 5H are cross-sectional views of an array substrate corresponding to the line V-V' of FIG. 4 and show cross-sections in steps of manufacturing an array substrate for an SOC-type LCD device according to the present invention.

[0079] FIG. 5A shows the array substrate in a first mask process. In FIG. 5A, a first switching region **S1**, first and second pixel regions **P1** and **P2**, first and second common regions **C1** and **C2**, a first gate region **G1** and a second data

region **D2** are defined on a substrate **110**. A first gate line **120a**, a second gate line **120b**, a first gate electrode **125a** and a second gate electrode **125b** of FIG. 4 are formed on the substrate **110** including the regions **S1**, **P1**, **P2**, **C1**, **C2**, **G1** and **D2** by depositing a gate metal layer (not shown) and then patterning the gate metal layer. At the same time, a first common line **150** and a second common line **151** are formed on the substrate **110**. The first gate line **120a** and the second gate line **120b** are formed along a first direction. The first gate line **120a** and the second gate line **120b** are spaced apart from and parallel with each other. The first gate electrode **125a** and the second gate electrode **125b** of FIG. 4 extend from the second gate line **120b**. Also, gate electrodes (not shown) extend from the first gate line **120a**. The first common line **150** corresponds to the first common region **C1**, and the second common line **151** corresponds to the second common region **C2**.

[0080] The first common line **150** includes a horizontal part **150a**, a first vertical part **150b** of FIG. 4 and a second vertical part **150c**. The horizontal part **150a** is formed along the first direction and is disposed in the first pixel region **P1** between the first and second gate lines **120a** and **120b**. The first vertical part **150b** of FIG. 4 and the second vertical part **150c** extend from respective ends of the horizontal part **150a** along a second direction. The second vertical part **150c** is disposed in the second data region **D2**.

[0081] The second common line **151** includes a horizontal part **151a** of FIG. 4, a first vertical part **151b** and a second vertical part **151c** of FIG. 4. The horizontal part **151a** is formed along the first direction and is disposed in the second pixel region **P2** between the first and second gate lines **120a** and **120b**. The first vertical part **151b** and the second vertical part **151c** of FIG. 4 extend from respective ends of the horizontal part **151a** along the second direction. The first vertical part **151b** is disposed in the second data region **D2**.

[0082] Here, the second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** entirely covers the second data region **D2** excluding a crossing region of the first gate line **120a** and a second data line to be formed later and a crossing region of the second gate line **120b** and the second data line, that is, the first switching region **S1** and another switching region (not shown). More particularly, the second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** contact each other in the second data region **D2**.

[0083] Accordingly, the first and second common lines **150** and **151** are electrically connected to other common lines in pixel regions adjacent to the first and second pixel regions **P1** and **P2**. A common signal from a common signal generating unit (not shown) is stably applied to the common lines.

[0084] Next, a gate insulating layer **145** is formed on a substantially entire surface of the substrate **110** including the first gate line **120a**, the second gate line **120b**, the first gate electrode **125a**, the second gate electrode **125b**, the first common line **150** and the second common line **151**. The gate insulating layer **145** may be formed of one selected from an inorganic insulating material group including silicon oxide (SiO_2) and silicon nitride (SiN_x).

[0085] FIGS. 5B to 5H show the array substrate in a second mask process.

[0086] In FIG. 5B, an intrinsic amorphous silicon layer **140a** and an impurity-doped amorphous silicon layer **141a** are sequentially formed on the substrate **110** including the

gate insulating layer **145**. The intrinsic amorphous silicon layer **140a** is formed of intrinsic amorphous silicon (a-Si:H), and the impurity-doped amorphous silicon layer **141a** is formed of amorphous silicon including impurities (n+ a-Si:H). A source and drain metal layer **175** is formed on the substrate **110** including the intrinsic amorphous silicon layer **140a** and the impurity-doped amorphous silicon layer **141a** by depositing a metallic material. The metallic material may be selected from a conductive metallic material group including copper (Cu), molybdenum (Mo), molybdenum alloy (MoNd), aluminum (Al) and aluminum alloy (AlNd).

[0087] That is, the intrinsic amorphous silicon layer **140a**, the impurity-doped amorphous silicon layer **141a** and the source and drain metal layer **175** are sequentially formed on the gate insulating layer **145** by a deposition process.

[0088] Next, a photoresist layer **190** is formed by applying photoresist to the substrate **110** including the intrinsic amorphous silicon layer **140a**, the impurity-doped amorphous silicon layer **141a** and the source and drain metal layer **175**, and a mask HTM is disposed over the photoresist layer **190**.

[0089] The mask HTM includes a light-transmitting portion M1, a half light-transmitting portion M2 and a light-blocking portion M3. The half light-transmitting portion M2 may include a semitransparent layer or slits for reducing the intensity or amount of transmitted light such that a photoresist layer is partially exposed to light. The mask HTM including the semitransparent layer may be referred to as a halftone mask, and the mask HTM including the slits may be referred to as a slit mask. The light-blocking portion M3 completely screens light. The light-transmitting portion M1 transmits light, and a photoresist layer is entirely exposed to light and is chemically changed.

[0090] The half light-transmitting portion M2 and the light-blocking portion M3 correspond to the first switching region S1 such that the half light-transmitting portion M2 is disposed between adjacent parts of the light-blocking portion M3. The light-blocking portion M3 also corresponds to the second data region D2. The light-transmitting portion M1 corresponds to other regions excluding the first switching region S1 and the second data region D2. Meanwhile, the mask HTM is disposed over a second switching region (not shown) corresponding to the second thin film transistor T2 of FIG. 4, a first data region (not shown) corresponding to the first data line **130a**, and a third data region (not shown) corresponding to the third data line **130c** in the same way as the first switching region S1 and the second data region D2 of FIG. 5B. Hereinafter, explanation of the second switching region and the first and third data regions will be omitted.

[0091] In FIG. 5C, the photoresist layer **190** of FIG. 5B is exposed to light through the mask HTM of FIG. 5B and then is developed, thereby forming first, second, third and fourth photoresist patterns **191**, **192**, **193** and **194**. The first and second photoresist patterns **191** and **192** are formed in the first switching region S1 corresponding to the light-blocking portion M3 of FIG. 5B. The third photoresist pattern **193** is formed in the first switching region S1 corresponding to the half light-transmitting portion M2 of FIG. 5B. The fourth photoresist pattern **194** is formed in the second data region D2. The first, second and fourth photoresist patterns **191**, **192** and **194** have a first thickness that is substantially same as a thickness of the photoresist layer **190** of FIG. 5B. The third photoresist pattern **193** has a second thickness smaller than the first thickness. The second thickness may be half of the first thickness. In other regions excluding the first switching

region S1 and the second data region D2, parts of the photoresist layer **190** of FIG. 5B are removed, and the source and drain metal layer **175** is exposed.

[0092] In FIG. 5D, the exposed source and drain metal layer **175** of FIG. 5C is patterned by using the first, second, third and fourth photoresist patterns **191**, **192**, **193** and **194** as an etching mask, and thus a first source and drain metal pattern **174a** and a second data line **130b** are formed in the first switching region S1 and the second data region D2, respectively. The second data line **130b** crosses the first and second gate lines **120a** and **120b**.

[0093] Here, the source and drain metal layer **175** of FIG. 5C is removed in regions excluding the first source and drain metal layer **175** and the second data line **130b**, and thus the impurity-doped amorphous silicon layer **141a** of FIG. 5C is exposed.

[0094] Next, the exposed impurity-doped amorphous silicon layer **141a** of FIG. 5C and the intrinsic amorphous silicon layer **140a** of FIG. 5C are removed and patterned by a dry etch method, thereby forming a first active layer **140a**, a first ohmic contact layer **141a**, a second intrinsic amorphous silicon pattern **171b** and a second impurity-doped amorphous silicon pattern **172b**. At this time, the first active layer **140a** and the ohmic contact layer **141a** are disposed under the first source and drain metal pattern **174a** in the first switching region S1 and have the same size and the same shape as the first source and drain metal pattern **174a**. The second intrinsic amorphous silicon pattern **171b** and the second impurity-doped amorphous silicon pattern **172b** are under the second data line **130b** in the second data region D2 and have the same size and the same shape as the second data line **130b**.

[0095] The first active layer **140a** and the first ohmic contact layer **141a** constitute a first semiconductor layer **141a**. The second intrinsic amorphous silicon pattern **171b** and the second impurity-doped amorphous silicon pattern **172b** constitute a second semiconductor pattern **173b**. Here, the intrinsic amorphous silicon layer **140a** of FIG. 5C and the impurity-doped amorphous silicon layer **141a** of FIG. 5C are removed in regions excluding the first semiconductor layer **142a** and the second semiconductor pattern **173b**. Meanwhile, although not shown in the figure, a first semiconductor pattern and a third semiconductor pattern are formed under the first data line **130a** of FIG. 4 and the third data line **130c** of FIG. 4.

[0096] In FIG. 5E, a process of ashing the first, second, third and fourth photoresist patterns **191**, **192**, **193** and **194** of FIG. 5D is performed, and the third photoresist pattern **193** of FIG. 5D is removed to expose the first source and drain metal pattern **174a** between the first and second photoresist patterns **191** and **192**. At this time, the first, second and fourth photoresist patterns **191**, **192** and **194** are partially removed, and the first thickness of the first, second and fourth photoresist patterns **191**, **192** and **194** is decreased by half.

[0097] In the meantime, edges of the first, second and fourth photoresist patterns **191**, **192** and **194** are also removed to expose edges F of the first source and drain metal pattern **174a** and the second data line **130b**. In addition, a distance between the first and second photoresist patterns **191** and **192** becomes larger than a width of the third photoresist pattern **193** of FIG. 5D.

[0098] In FIG. 5F, a first source electrode **132a** and a first drain electrode **134a** are formed by patterning the first source and drain metal pattern **174a** of FIG. 5E using the first, second and fourth photoresist patterns **191**, **192** and **194** of FIG. 5E as

an etching mask. The first source electrode **132a** and the first drain electrode **134a** are spaced apart from each other. The first source and drain metal pattern **174a** of FIG. 5E may be patterned by a wet etch method. Next, the first ohmic contact layer **141a** between the first source electrode **132a** and the first drain electrode **134a** is removed by using the first source electrode **132a** and the first drain electrode **134a** as an etching mask, thereby forming separated two parts of the first ohmic contact layer **141a** and exposing the first active layer **140a** between the two parts of the first ohmic contact layer **141a**. The exposed first active layer **140a** functions as a first channel ch1. The exposed first active layer **140a** may be partially removed.

[0099] At this time, the edges F of the first source and drain metal pattern **174a** and the second data line **130b** and the first ohmic contact layer **141a** and the first impurity-doped amorphous silicon pattern **172** thereunder are also removed, and edges of the first active layer **140a** and the first amorphous silicon pattern **171a** are exposed beyond the first source electrode **132a**, the first drain electrode **134a** and the second data line **130b**. The first gate electrode **125a**, the first semiconductor layer **142a**, the first source electrode **132a** and the first drain electrode **134a** constitute a first thin film transistor T1. [0100] Next, the remaining first, second and fourth photoresist patterns **191**, **192** and **194** of FIG. 5E are removed by a strip process.

[0101] FIG. 5G shows the array substrate in a third mask process.

[0102] In FIG. 5G, a passivation layer **155** is formed on a substantially entire surface of the substrate **110** including the second data line **130b** and the first thin film transistor T1. The passivation layer **155** may be formed of one selected from an inorganic insulating material group including silicon nitride (SiN_x) and silicon oxide (SiO_2) or an organic insulating material group including benzocyclobutene (BCB) and photo acryl.

[0103] The passivation layer **155** corresponding to the first drain electrode **134a** and the second drain electrode **134b** of FIG. 4 is selectively patterned to form a first drain contact hole CH1 and a second drain contact hole CH2 of FIG. 4. The first drain contact hole CH1 exposes the first drain electrode **134a**, and the second drain contact hole CH2 of FIG. 4 exposes the second drain electrode **134b** of FIG. 4.

[0104] FIG. 5H shows the array substrate in a fourth mask process.

[0105] In FIG. 5H, a first pixel electrode **170a** and a second pixel electrode **170b** are formed on the passivation layer **155** including the first drain contact hole CH1 and the second drain contact hole CH2 of FIG. 4 by depositing a transparent conductive layer (not shown) and then patterning the transparent conductive layer. The first pixel electrode **170a** is disposed in the first pixel region P1 and is connected to the first drain electrode **134a** through the first drain contact hole CH1. The second pixel electrode **170b** is disposed in the second pixel region P2 and is connected to the second drain electrode **134b** of FIG. 4 through the second contact hole CH2 of FIG. 4. The transparent conductive layer may be selected from a transparent conductive material group including indium tin oxide (ITO) and indium zinc oxide (IZO).

[0106] At this time, referring to FIG. 4 and FIG. 5H, a first storage capacitor Cst1 and a second storage capacitor Cst2 are formed. The first storage capacitor Cst1 includes the horizontal part **150a** and the first and second vertical parts **150b** and **150c** of the first common line **150** as a first electrode, the

first pixel electrode **170a** overlapping the first electrode as a second electrode, and the gate insulating layer **145** and the passivation layer **155** interposed between the first and second electrodes as a dielectric layer.

[0107] In addition, the second storage capacitor Cst2 includes the horizontal part **151a** and the first and second vertical parts **151b** and **151c** of the second common line **151** as a first electrode, the second pixel electrode **170b** overlapping the first electrode as a second electrode, and the gate insulating layer **145** and the passivation layer **155** interposed between the first and second electrodes as a dielectric layer.

[0108] Like this, the array substrate for an SOC-type LCD device according to the present invention may be manufactured by four mask processes.

[0109] FIG. 6 is a cross-sectional view of an SOC-type LCD device according to the present invention and corresponds to a cross-section taken along the line VI-VI' of FIG. 4.

[0110] In FIG. 6, a color filter substrate **105** and an array substrate **110** are facing each other and attached with a cell gap g therebetween. Each of the color filter substrate **105** and the array substrate **110** includes a display area AA and a non-display area NAA. A liquid crystal layer **115** is interposed between the color filter substrate **105** and the array substrate **110**. The liquid crystal layer **115** has a thickness corresponding to the cell gap g. The color filter substrate **105**, the array substrate **110** and the liquid crystal layer **115** constitute a liquid crystal panel **130**. A backlight unit **190** is disposed at a rear surface of the array substrate **110** as a light source.

[0111] Even though not shown in the figure, a seal pattern is formed between the color filter substrate **105** and the array substrate **110** along peripheries. The seal pattern may be formed of a thermosetting resin.

[0112] The color filter substrate **105** includes a transparent substrate **101**, a black matrix **112**, a color filter layer **116**, an overcoat layer **114** and a common electrode **180**. The black matrix **112** is formed at a lower surface of the transparent substrate **101** and screens light incident on the non-display area NAA. The color filter layer **116** is formed on the black matrix **112** and includes a red sub color filter **116a**, a green sub color filter **116b** and a blue sub color filter (not shown) that are subsequently patterned. The overcoat layer **114** is formed on the color filter layer **116**. The common electrode **180** is formed on the overcoat layer **114** and is formed of a transparent conductive material.

[0113] The array substrate **110** includes a transparent substrate **102**, a second vertical part **150c** of a first common line **150**, the first vertical part **151b** of the second common line **151**, the gate insulating layer **145**, the second data line **130b**, the passivation layer **155**, and the first and second pixel electrodes **170a** and **170b**. The second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** are formed on an upper surface of the transparent substrate **102** and contact each other to cover the second data region D2. The gate insulating layer **145** covers the second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151**. The second data line **130b** is disposed in the second data line D2 on the gate insulating layer **145**. The passivation layer **155** covers the second data line **130b**. The first and second pixel electrodes **170a** and **170b** are formed on the passivation

layer **155** in the first and second pixel regions **P1** and **P2**, respectively, such that the second data line **130b** is disposed therebetween.

[0114] In the SOC-type LCD device according to the present invention, since the second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** are designed to contact each other under the second data line **130b**, the common bridge lines are not needed.

[0115] That is, in the related art of FIG. 3, the second vertical part **50c** of the first common line **50** and the first vertical part **51b** of the second common line **51** are disposed at both sides of the second data line **30b** and spaced apart from each other to minimize an overlapping area between the second data line **30** and the second vertical part **50c** of the first common line **50** and an overlapping area between the second data line **30** and the first vertical part **50b** of the second common line **51**.

[0116] On the other hand, in the present invention, the second vertical part **150c** of the first common line **150** and the first vertical part **151b** of the second common line **151** are formed to contact each other under the second data line **130b**, and thus it is possible to decrease areas that the first common line **151** and the second common line **151** occupy in the first and second pixel regions **P1** and **P2**, respectively.

[0117] Accordingly, the first pixel electrode **170a** and the second pixel electrode **170b** are designed to be closer to the second data line **130b**, and sizes of the first pixel electrode **170a** and the second pixel electrode **170b** in the first and second pixel regions **P1** and **P2** increase. This causes a decrease in a width of the black matrix **112** as compared with the related art even if an attachment margin is considered. Therefore, the aperture ratio is increased.

[0118] Particularly, remarkable effects can be obtained when the SOC-type LCD device according to the present invention is applied to a small-sized device of less than 10 inches.

[0119] Table 1 shows aperture ratios and transmittances of SOC-type LCD devices according to the related art and the present invention. Here, the devices have a 7 inch size.

TABLE 1

	related art	present invention
L1	42.5%	60.9%
L2	42.5%	58.9%
L3	6.04%	8.36%

[0120] In table 1, L1 and L2 show a percentage of the aperture ratio when light from the backlight unit is provided to the liquid crystal panel. L1 is a maximum value in deviation of the aperture ratio of the related art and the present invention, and the aperture ratio of the present invention increases by 18.5% in comparison to the related art. L2 is an average value of the aperture ratio of the related art and the present invention, and the aperture ratio of the present invention increases by 16.4% as compared with the related art.

[0121] Meanwhile, L3 shows a percentage of an average value of the transmittance of an LCD device including the liquid crystal panel, polarizers and optical sheets. The transmittance of the present invention increases by 2.32% in comparison to the related art.

[0122] In the present invention, the first common line and the second common line contacts each other in the data line, and thus the aperture ratio of the SOC-type LCD device is maximized.

[0123] Even though the first and second pixels are described as an embodiment of the present invention, the first and second pixels may have the same structure, and one pixel structure may be repeatedly included. More particularly, a gate line and a data line cross each other and define a pixel region. A thin film transistor is connected to the gate and data lines. A pixel electrode is formed in the pixel region and is connected to the thin film transistor. A common line including a horizontal portion.

[0124] It will be apparent to those skilled in the art that various modifications and variation can be made in the present invention without departing from the spirit or scope of the invention. Thus, it is intended that the present invention cover the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An array substrate for a liquid crystal display device, comprising:

a substrate;

first and second gate lines along a first direction on the substrate;

first, second and third data lines along a second direction and crossing the first and second gate lines to define first and second pixel regions;

first and second thin film transistors at a crossing portion of the second gate line and the first data line and at a crossing portion of the second gate line and the second data line, respectively;

first and second pixel electrodes in the first and second pixel regions, respectively, the first pixel electrode connected to the first thin film transistor and the second pixel electrode connected to the second thin film transistor; and

first and second common lines between the first and second gate lines, the first and second common lines overlapping the first and second pixel electrodes, respectively, and connected to each other under the second data line to cover a part of the second data line between the first and second gate lines.

2. The array substrate according to claim 1, wherein each of the first common line and the second common line includes a horizontal portion, a first vertical portion, and a second vertical portion, the horizontal portion disposed along the first direction, the first and second vertical portions extending from the horizontal portion along the second direction, wherein the first and second vertical portions of the first common line overlap the first and second data lines, the first and second vertical portions of the second common line overlap the second and third data lines.

3. The array substrate according to claim 2, wherein the second vertical portion of the first common line overlaps the first vertical portion of the second common line under the second data line.

4. The array substrate according to claim 2, wherein the horizontal portion and the first and second vertical portions of the first common line as a first electrode, the first pixel electrode as a second electrode, and an insulating layer interposed therebetween constitute a first storage capacitor.

5. The array substrate according to claim 4, wherein the horizontal portion and the first and second vertical portions of the second common line as a first electrode, the second pixel electrode as a second electrode, and an insulating layer interposed therebetween constitute a second storage capacitor.

6. A method of manufacturing an array substrate for a liquid crystal display device, comprising:

defining first and second switching regions, first and second pixel regions, first and second common regions, and first, second and third data regions on a substrate;

forming first and second gate lines, first and second gate electrodes, and first and second common lines on the substrate, wherein the first and second gate lines are formed along a first direction, the first and second gate electrodes are connected to the second gate line, and the first and second common lines are disposed in the first and second common regions, respectively;

forming a gate insulating layer on the first and second gate lines, the first and second gate electrodes, and the first and second common lines;

forming first and second semiconductor layers on the gate insulating layer over the first and second gate electrodes; forming first, second and third data lines, first and second source electrodes, and first and second drain electrodes over the first and second semiconductor layers, wherein the first, second and third data lines are formed along a second direction and cross the first and second gate lines to define the first and second pixel regions, the first source and drain electrodes are spaced apart from each other over the first semiconductor layer, and the second source and drain electrodes are spaced apart from each other over the second semiconductor layer;

forming a passivation layer on the first, second and third data lines, the first and second source electrodes, and the first and second drain electrodes, the passivation layer including first and second contact holes that expose the first and second drain electrodes, respectively; and

forming first and second pixel electrodes on the passivation layer, the first pixel electrode connected to the first drain electrode through the first contact hole, and the second pixel electrode connected to the second drain electrode through the second contact hole,

wherein the first and second common lines overlap the first and second pixel electrodes, respectively, and are connected to each other under the second data line to cover a part of the second data line between the first and second gate lines.

7. The method according to claim 6, wherein each of the first common line and the second common line includes a horizontal portion, a first vertical portion, and a second vertical portion, the horizontal portion disposed along the first direction, the first and second vertical portions extending from the horizontal portion along the second direction, wherein the first and second vertical portions of the first common line overlap the first and second data lines, the first and second vertical portions of the second common line overlap the second and third data lines.

8. The method according to claim 7, wherein the horizontal portion and the first and second vertical portions of the first common line as a first electrode, the first pixel electrode as a second electrode, and an insulating layer interposed therebetween constitute a first storage capacitor.

9. The method according to claim 8, wherein the horizontal portion and the first and second vertical portions of the second common line as a first electrode, the second pixel electrode as a second electrode, and an insulating layer interposed therebetween constitute a second storage capacitor.

10. The method according to claim 6, wherein a step of forming the first and second semiconductor layers is performed in a same process as a step of forming the first, second and third data lines, the first and second source electrodes, and the first and second drain electrodes.

11. An array substrate for a liquid crystal display device, comprising:

a substrate;

a gate line along a first direction on the substrate;

a data line along a second direction and crossing the gate line to define a pixel region;

a thin film transistor at a crossing portion of the gate line and the data line;

a pixel electrode in the pixel region and connected to the thin film transistor; and

a common line between adjacent gate lines and overlapping the pixel electrode, the common line including a horizontal portion along the first direction and first and second vertical portions along the second direction, wherein the first vertical portion of the common line directly contacts a second vertical portion of a common line in a next pixel region under the data line to thereby cover a part of the data line between the adjacent gate lines.

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专利名称(译)	用于液晶显示装置的阵列基板及其制造方法		
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摘要(译)

一种LCD装置，包括：基板，沿第一方向的第一和第二栅极线，沿第二方向的第一至第三数据线，并且与第一和第二栅极线交叉以限定第一和第二像素区域，第一和第二TFT在交叉处第二栅极线和第一数据线以及第二栅极线和第二数据线的交叉，第一和第二像素区域中的第一和第二像素电极，第一像素电极连接到第一TFT和第二像素电极连接到第二TFT，以及第一和第二栅极线之间的第一和第二公共线，并且与第一和第二像素电极重叠，并且在第二数据线下彼此连接以覆盖第一数据线之间的第二数据线的一部分和第二条栅极线。

